### **Course Info**

- Course focuses on design an modeling of "high frequency" power electronics
  - Course website: http://web.eecs.utk.edu/~dcostine/ECE581
  - Goal of course is understanding of motivations and issues with high frequency power electronics; analysis and design techniques; applications
- Prerequisites: undergraduate Circuits sequence,
  Microelectronics, ECE 481 Power Electronics, or equivalent



### **Contact Info**

**Instructor:** Daniel Costinett

• Office: MK504

• Office Hours: W 3-4pm, R 10-11am

• E-mail: Daniel.Costinett@utk.edu

- Email questions will be answered within 24 hours (excluding weekends)
- Please use [ECE 581] in the subject line

### **Course Structure**

- Course meets MWF 9:15-10:05 am
- Plan to spend ~9 hours per week on course outside of lectures
- Grading:
  - Homework/Lab: 40%
    - One homework per week
    - · Assignments due on Fridays unless otherwise noted on course website
  - Midterm: 25%
    - Tentatively scheduled for October 29th
  - Final: 35%



### **Assignments**

- Assignments due at the start of lecture on the day indicated on the course schedule
- All assignments submitted through canvas
  - https://utk.instructure.com/courses/104569
- No late work will be accepted except in cases of documented medical emergences
- Collaboration is encouraged on all assignments except exams; Turn in your own work
- All work to be turned in through canvas

### **Textbook and Materials**

The textbook

R.Erickson, D.Maksimovic, *Fundamentals of Power Electronics*, Springer 2001

will cover some of chapters 19-20 and reference materials from prior chapters. The textbook is available on-line from campus network. Purchase is not required for this course.

- MATLAB/Simulink, LTSpice will be used; All installed in the Tesla Lab
- Lecture slides and notes, additional course materials, homework, due dates, etc. posted on the course website
- Additional information on course website



### **Online Tools**

- Zoom
  - https://tennessee.zoom.us/j/94031104264
  - All lectures will be livestreamed and recorded through the same zoom meeting
- Slack
  - https://curenterc.slack.com/archives/G019PH31YP2
  - Peer collaboration, and instructor-student communication
- Canvas
  - https://utk.instructure.com/courses/104569
  - Submission of all assignments
- Slido
  - https://app.sli.do/event/lhsyh9vk/live/questions
  - Anonymous feedback / Q&A during lectures

### **Office Hours**

- In-person office hours not permitted
- Scheduled office hours are times of maximum availability
- Contact me by e-mail, slack to start a telecon
- Outside of office hours, I will respond within
  24 hours to e-mail or slack messages

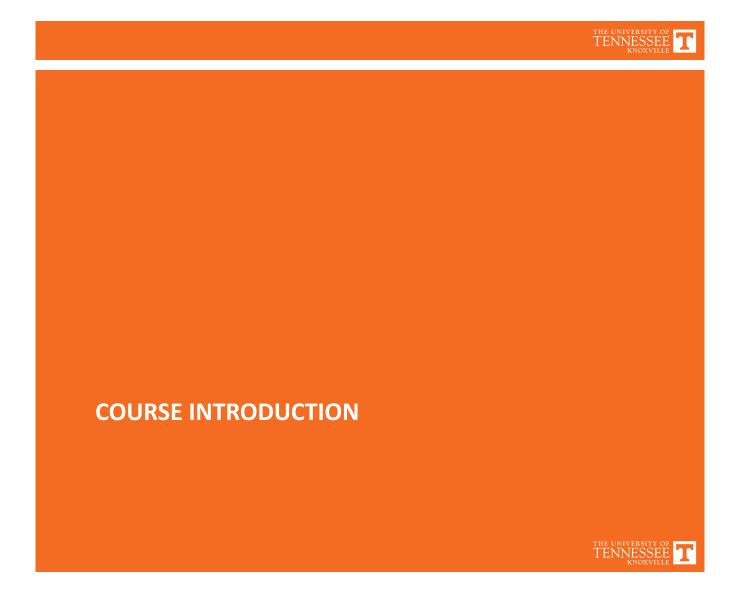


# TINY BOX CHALLENGE

- Design competition to build and test an "optimized" dc-dc converter
  - Fall '16 60-to-12V, 60W
  - Fall '18 48-to-1.2V, 12W
- Format and feasibility TBD due to labwork requirement
  - Usually ~October-November
  - Usually in groups of 2-3

# **Pandemic Planning**

Discussion



### Introduction

- Why high frequency?
  - Power Density
  - Control Bandwidth
- Techniques
  - Devices
  - Control
  - Topologies
  - Passives





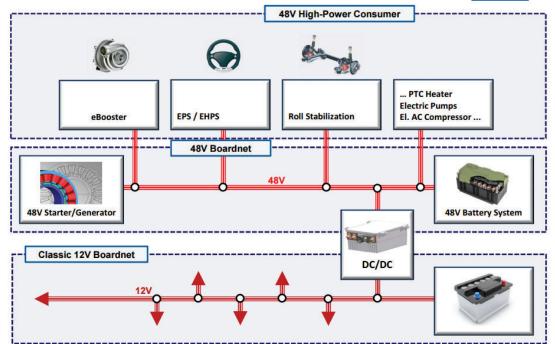
Voltage Regulation Module



# **Motivating Example**

AVL

#### 12V/48V Electrical Architecture

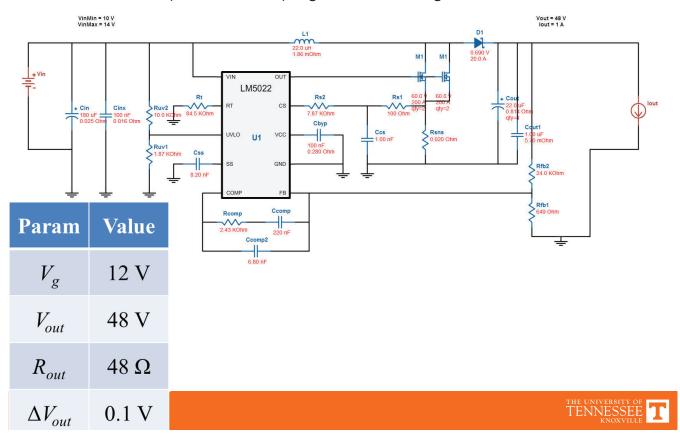


AVL UK Expo 2014 / Ulf Stenzel

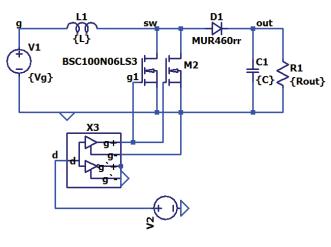


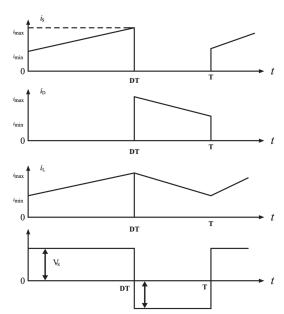
## **Baseline Design**

• Use TI WebBench (webench.ti.com) to get a baseline design



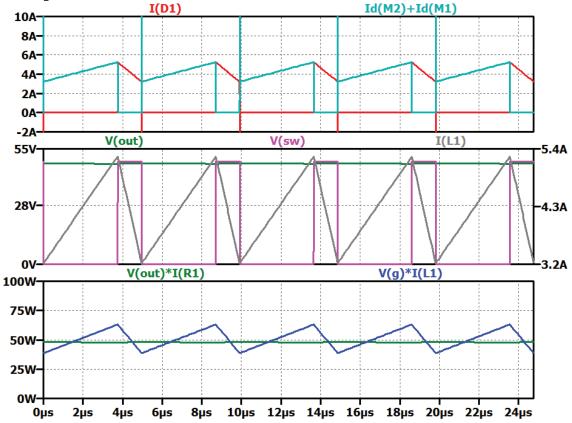
# **LTSpice Simulation**





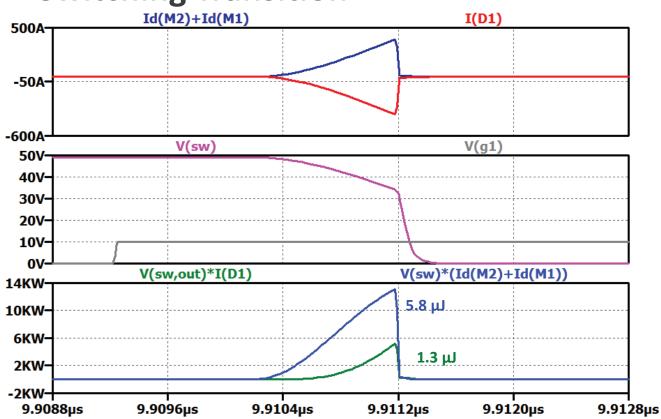
L	Cout	$f_s$	Diode	η (Sim)
22uH	22uF	202k	Si (FR)	93.9%

### **LTSpice Simulation**

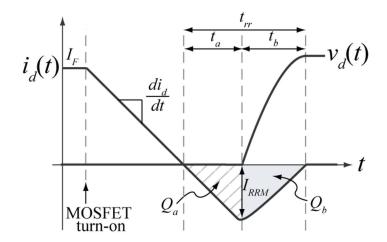


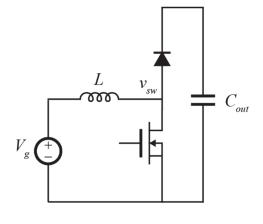
THE UNIVERSITY OF TENNESSEE

# **Switching Transition**



# **Diode Reverse Recovery**







### **Datasheet RR Characteristics**

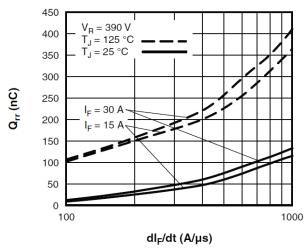


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

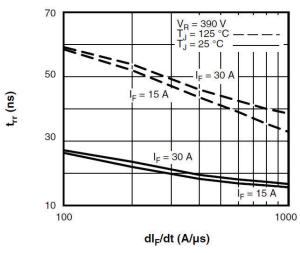
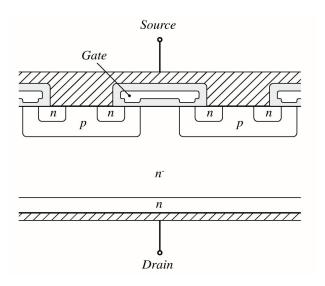
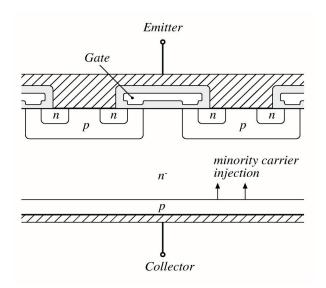


Fig. 9 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

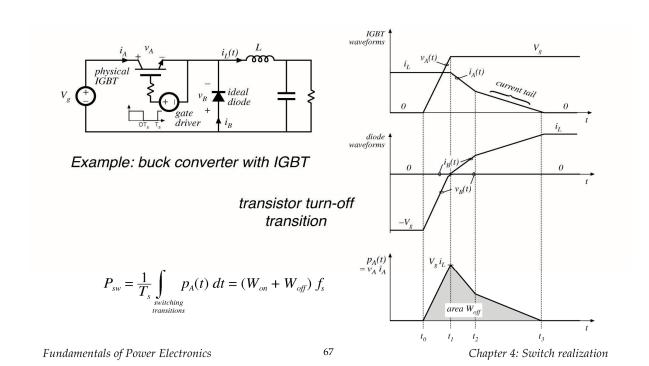
# **Charge Storage**



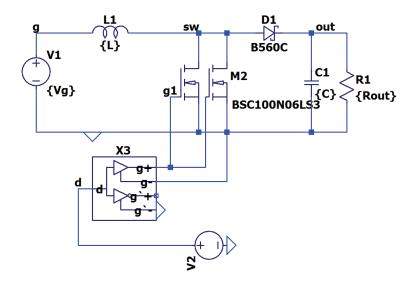




# **IGBT Current Tailing**



# **Schottky Diode**



L	C <sub>out</sub>	$f_s$	Diode	η (Sim)
22uH	22uF	202k	Si (FR)	93.9%
22uH	22uF	202k	Si Schottky	95.8%

